

## **SiC JFET Division**

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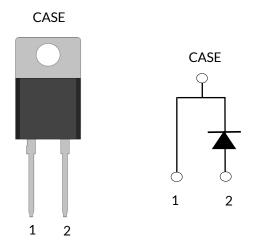








# **UJ3D1205TS**



Part Number	Package	Marking
UJ3D1205TS	TO-220-2L	UJ3D1205TS











# Silicon Carbide (SiC) Diode - EliteSiC, TO-220-2L, 5 A, 1200 V SiC Merged PiN-Schottky (MPS) Diode

Rev. D, Jan 2025

#### Description

UnitedSiC offers the  $3^{rd}$  generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and  $175^{\circ}$ C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.

#### **Features**

- Maximum operating temperature of 175°C
- Easy paralleling
- Extremely fast switching not dependent on temperature
- No reverse or forward recovery
- Enhanced surge current capability, MPS structure
- Excellent thermal performance, Ag sintered
- 100% UIS tested
- AEC-Q101 qualified

#### **Typical applications**

- Power converters
- Industrial motor drives
- Switch mode power supplies
- Power factor correction modules













## **Maximum Ratings**

Parameter	Symbol	Test Conditions	Value	Units	
DC blocking voltage	$V_R$		1200	V	
Repetitive peak reverse voltage, T <sub>J</sub> =25°C	$V_{RRM}$		1200	V	
Surge peak reverse voltage	$V_{RSM}$		1200	V	
Maximum DC forward current	I <sub>F</sub>	$T_{C} = 160.7^{\circ}C$	5	Α	
Non-repetitive forward surge current	1	$T_C = 25$ °C, $t_p = 10$ ms	70	Α	
sine halfwave	I <sub>FSM</sub>	$T_C = 110^{\circ}C, t_p = 10 \text{ms}$	63		
Repetitive forward surge current	1	$T_C = 25$ °C, $t_p = 10$ ms	31.8		
sine halfwave, D=0.1	I <sub>FRM</sub>	$T_C = 110^{\circ}C, t_p = 10 \text{ms}$	18.6	Α	
Non-repetitive peak forward current	I <sub>F,max</sub>	$T_C = 25^{\circ}C, t_p = 10 \mu s$	525		
		$T_C = 110^{\circ}C, t_p = 10\mu s$	525	Α	
•2.	∫i²dt	$T_C = 25$ °C, $t_p = 10$ ms	24.5	^2-	
i <sup>2</sup> t value		$T_C = 110^{\circ}C, t_p = 10 \text{ms}$	19.5	$A^2$ s	
Power dissipation	P <sub>tot</sub>	T <sub>C</sub> = 25°C	136	14/	
		T <sub>C</sub> = 160.7°C	13	W	
Maximum junction temperature	$T_{J,max}$		175	°C	
Operating and storage temperature	$T_J,T_STG$		-55 to 175	°C	
Soldering temperatures, wavesoldering only allowed at leads	T <sub>sold</sub>	1.6mm from case for 10s	260	°C	

### **Thermal Characteristics**

Parameter	Symbol	Test Conditions	Value			- Units
Parameter			Min	Тур	Max	Offics
Thermal resistance, junction-to-case	$R_{ heta$ JC			0.85	1.1	°C/W

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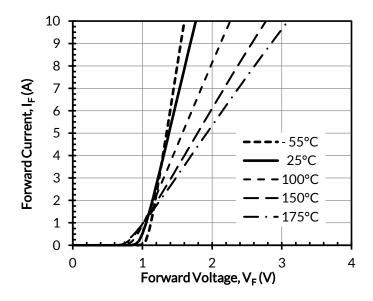


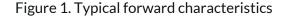
# Electrical Characteristics (T<sub>J</sub> = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Value			Units
			Min	Тур	Max	Units
Forward voltage	V <sub>F</sub>	$I_F = 5A, T_J = 25^{\circ}C$	-	1.4	1.6	V
		I <sub>F</sub> = 5A, T <sub>J</sub> =150°C	-	1.85	2.3	
		I <sub>F</sub> = 5A, T <sub>J</sub> =175°C	-	2	2.6	
Reverse current	I <sub>R</sub>	V <sub>R</sub> =1200V, T <sub>J</sub> =25°C	-	5	55	μΑ
		V <sub>R</sub> =1200V, T <sub>J</sub> =175°C	-	160		
Total capacitive charge <sup>(1)</sup>	Q <sub>C</sub>	V <sub>R</sub> =800V		27		nC
Total capacitance	С	$V_R=1V, f=1MHz$		250		pF
		V <sub>R</sub> =400V, f = 1MHz		24.5		
		V <sub>R</sub> =800V, f = 1MHz		22		
Capacitance stored energy	E <sub>C</sub>	V <sub>R</sub> =800V		8		μЈ

(1)  $Q_c$  is independent on  $T_J$ ,  $di_F/dt$ , and  $I_F$  as shown in the application note USCi\_AN0011.

### **Typical Performance Diagrams**





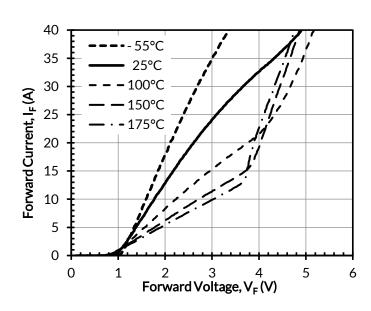


Figure 2. Typical forward characteristics in surge current

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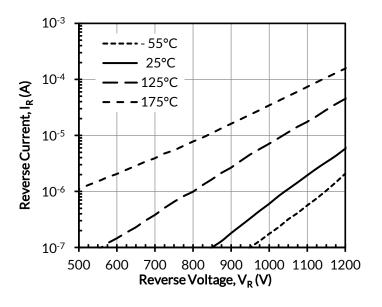












150
125

M roiteids:

75

25

50

25

50

75

100

125

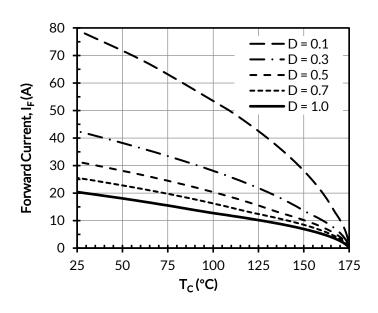
150

175

T<sub>c</sub>(°C)

Figure 3. Typical reverse characteristics

Figure 4. Power dissipation



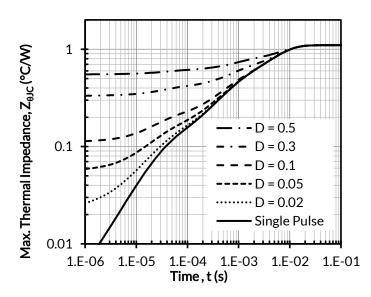


Figure 5. Diode forward current

Figure 6. Maximum transient thermal impedance



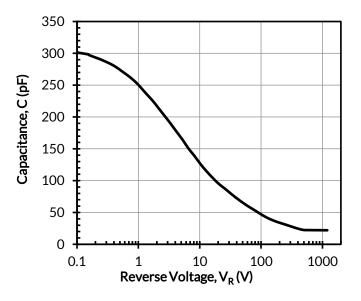












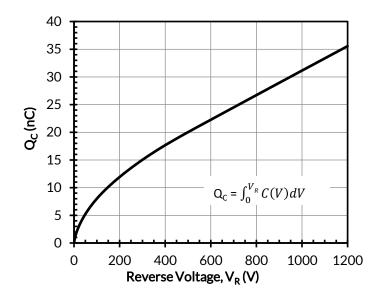


Figure 7. Capacitance vs. reverse voltage at 1MHz

Figure 8. Typical capacitive charge vs. reverse voltage

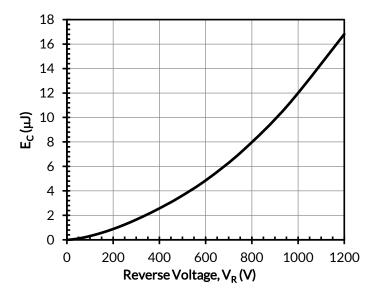


Figure 9. Typical capacitance stored energy vs. reverse voltage













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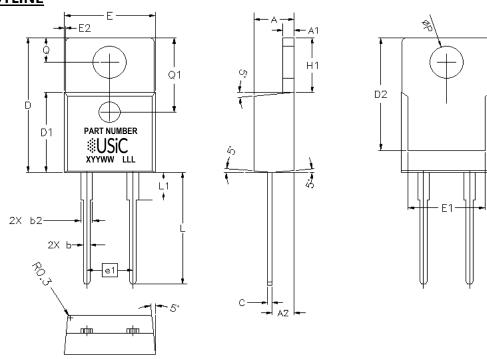
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# TO-220-2L PACKAGE OUTLINE, PART MARKING AND TUBE SPECIFICATIONS

#### **PACKAGE OUTLINE**

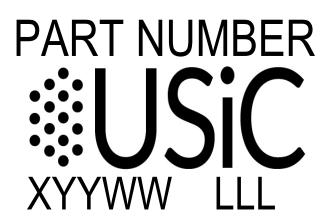


DIM	INC	HES	MILLIN	<b>METERS</b>
	MIN	MAX	MIN	MAX
Α	0.140	0.190	3.56	4.83
A1	0.020	0.055	0.51	1.40
A2	0.080	0.115	2.03	2.92
b	0.015	0.040	0.38	1.02
b2	0.040	0.070	1.02	1.78
С	0.014	0.030	0.36	0.76
D	0.560	0.650	14.22	16.51
D1	0.330	0.370	8.38	9.40
D2	0.480	0.517	12.19	13.13
E	0.380	0.420	9.65	10.67
e1	0.200 BSC		5.08	BSC
E1	0.270	0.350	6.86	8.89
E2	-	0.030		0.76
L	0.495	0.580	12.57	14.73
L1	-	0.250	1	6.35
ØΡ	0.139	0.161	3.53	4.09
Н	0.230	0.270	5.84	6.86
Q	0.100	0.135	2.54	3.43
Q1	0.330	0.340	8.38	8.64



# TO-220-2L PACKAGE OUTLINE, PART MARKING AND TUBE SPECIFICATIONS

#### **PART MARKING**



PART NUMBER = REFER TO
DS PN DECODER FOR DETAILS

X = ASSEMBLY SITE

YY = YEAR

WW = WORK WEEK

LLL = LOT ID

### **PACKING TYPE**

**ANTI-STATIC TUBE** 

**QUANTITY /TUBE: 50 UNITS** 

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